L Number	Hits	Search Text	DB	Time stamp
10	79354	mosfet (metal near oxide near semiconductor near field-effect near	USPAT; US-PGPUB;	2004/06/01 12:33
		transistor) (metal near oxide near semiconductor near field-effect near transistor) (mos with fet)	EPO; JPO; DERWENT; IBM TDB	
11	1131388	trench\$2 recess\$2 trough\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/01 12:34
12	36515	body adj2 (region area)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/01 12:34
13	54383	epitaxial near2 (layer film)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 12:35
17	57149	(polycrystal\$4 poly-crystal\$4) with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 12:45
18	306	<pre>(mosfet (metal near oxide near semiconductor near field-effect near transistor) (metal near oxide near semiconductor near field-effect near transistor) (mos with fet)) and (trench\$2 recess\$2 trough\$2) and (body adj2 (region area)) and (epitaxial near2 (layer film)) and ((polycrystal\$4 poly-crystal\$4) with silicon)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 12:45